

ISC Silicon NPN Power Transistor

2SC4235

DESCRIPTION

- · Collector-Emitter Sustaining Voltage-
 - : V_{CEO(SUS)}= 800V(Min)
- · Fast Switching speed
- 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

Color TV horizontal output applications



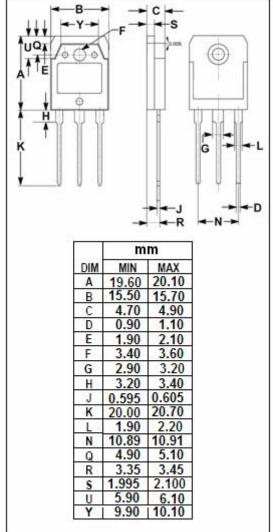
PIN 1. BASE 2.COLLECTOR 3. BMITTER TO-3PN package

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|---|---------|--------------|--|
| V _{CBO} | Collector-Base Voltage | 1200 | V | |
| V _{CEO} | Collector-Emitter Voltage | 800 | V | |
| V _{EBO} | Emitter-Base Voltage | 7 | V | |
| Ic | Collector Current-Continuous | 3 | А | |
| I _{CM} | Collector Current-Peak | 6 | А | |
| I _B | Base Current-Continuous | 1 | А | |
| Івм | Base Current-Peak | 2 | А | |
| P _T | Total Power Dissipation @ T _C =25°C | 80 | W | |
| TJ | Junction Temperature | 150 | $^{\circ}$ C | |
| T _{stg} | Storage Temperature Range | -55~150 | $^{\circ}$ C | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | | UNIT |
|---------------------|-------------------------------------|--|------|
| R _{th j-c} | Thermal Resistance,Junction to Case | | °C/W |



¹ isc & iscsemi is registered trademark isc Website: www.iscsemi.cn



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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | | |
|-----------------------|--------------------------------------|--|-----|------|-----|------|--|--|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 0.1A; I _B = 0 | 800 | | | V | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 1.5A; I _B = 0.3A | | | 1.0 | V | | |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 1.5A; I _B = 0.3A | | | 1.5 | V | | |
| I _{CBO} | Collector Cutoff Current | At rated Voltage | | | 100 | μА | | |
| I _{CEO} | Collector Cutoff Current | At rated Voltage | | | 100 | μА | | |
| I _{EBO} | Emitter Cutoff Current | At rated Voltage | | | 100 | μА | | |
| h _{FE-1} | DC Current Gain | Ic= 1.5A; V _{CE} = 5V | 8 | | | | | |
| h _{FE-2} | DC Current Gain | I _C = 1mA; V _{CE} = 5V | 7 | | | | | |
| f _T | Current-Gain—Bandwidth Product | I _C = 0.3A; V _{CE} = 10V | | 8 | | MHz | | |
| Switching times | | | | | | | | |
| ton | Turn-on Time | | | | 0.5 | μs | | |
| t _{stg} | Storage Time | I_{C} = 1.5A , I_{B1} = 0.3A; I_{B2} = -0.6A R_{L} = 170 Ω ; V_{BB2} = 4V | | | 3.5 | μS | | |
| t _f | Fall Time | | | | 0.3 | μS | | |

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